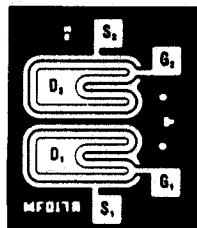


CHIP NUMBER

DFMP2



.035"
(0.889mm)

.029"
(0.737mm)

Die Size: 29 x 35 (mils)
0.737 x 0.889(mm)
5 x 5 (mils)
Pad Size: 0.127 x 0.127(mm)
BODY-SUBSTRATE

CONTACT METALLIZATION

Top Contact: > 12,000
Å Aluminum

Backside Contact: 3,000 Å Gold

ASSEMBLY RECOMMENDATIONS

It is advisable that:

- the die be eutectically mounted with gold silicon preform 98/2%.
- 1 mil (0.0254mm) aluminum wire be ultrasonically attached to the top contact.

TYPICAL ELECTRICAL CHARACTERISTICS

PARAMETER	MIN.	TYP	MAX.	UNIT	TEST CONDITIONS
BVDSS	-30		-60	V	$V_{GS} = 0, I_D = -10\mu A$
I_{DSS}		-10	-500	pA	$V_{DS} = -15V, V_{GS} = 0, V_{GB} = 0$
g_{fs}	1500		4000	μmho	$V_{DS} = -15V, I_D = -10mA, f = 1KHz$
I_{SDS}			350	pA	$V_{GD} = 0, V_{SD} = -15V, V_{DB} = 0$
r_{DS}			300	Ω	$V_{GS} = -20V, I_D = -100\mu A$
$V_{GS(th)}$	-1.5		-5.0	V	$V_{DS} = -15V, I_D = -100\mu A$
C_{rss}		.8	1.5	pF	$V_{DS} = -15V, I_D = -10\mu A, f = 1MHz$
C_{iss}		3.3	4.5	pF	$V_{DS} = -15V, I_D = -10mA, f = 1MHz$
$\bar{e}_n$		50		nV/ $\sqrt{Hz}$	$V_{DS} = -15V, I_D = -1mA, f = 1KHz$
$V_{GS(th) (1-2)}$		25	200	mV	$V_{DS} = -15V, I_D = -500\mu A$

TYPICAL DEVICE TYPES: 3N190, 3N191

FIGURE 1

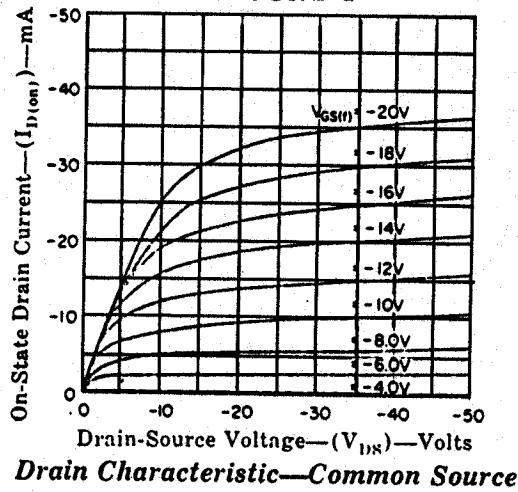


FIGURE 2

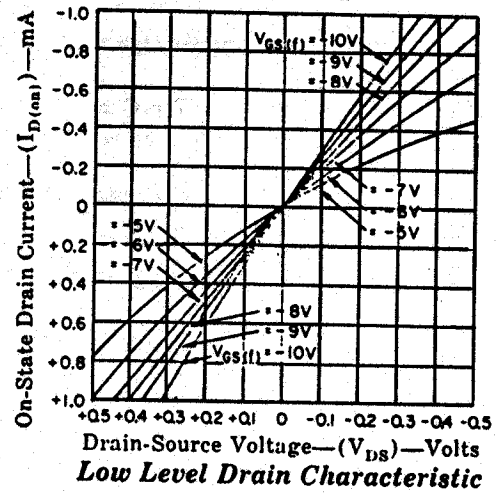


FIGURE 3

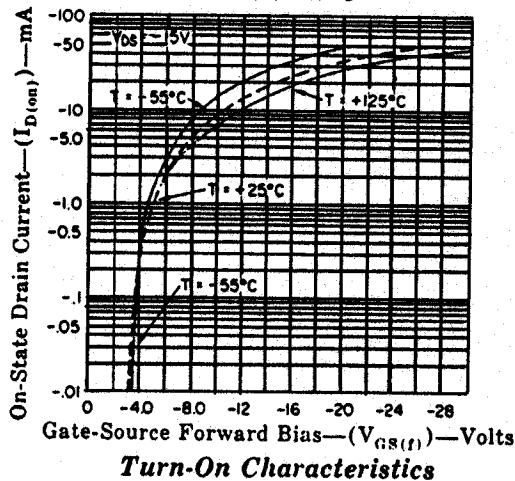


FIGURE 4

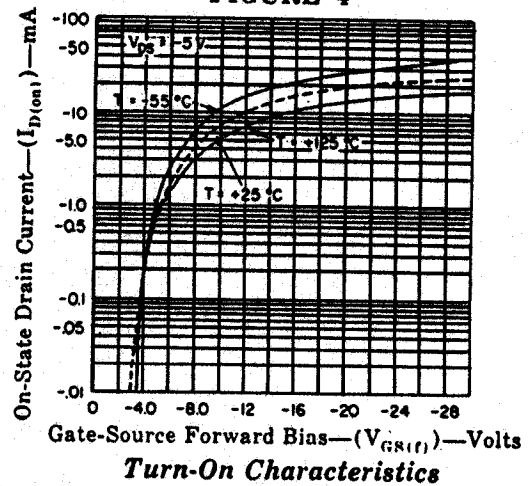


FIGURE 5

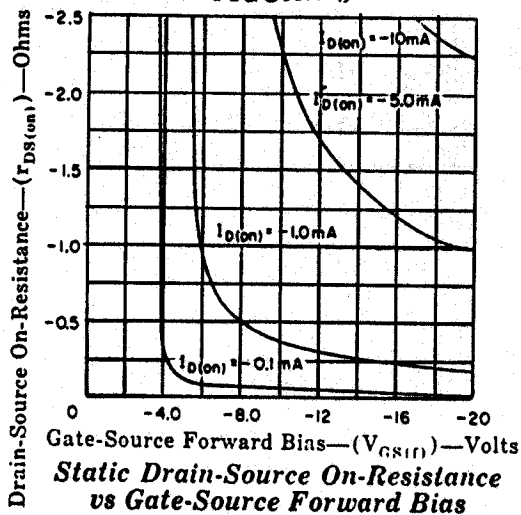


FIGURE 6

